CBCS SCHEME

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A CA			CMOS VLSI Design	
The state of the s	Tim	1e:13	hrs. Max. Max. Max. Max. Max. Max. Max. Max	arks: 80
MICOR	E - 37	The state of the		1
ઇ		No	ote: Answer any FIVE full questions, choosing ONE full question from each mod	dule.
s blank pages. = 50, will be treated as malpractice.			Module-1	
nalp	1	a.	State and explain Moore's law.	(04 Marks)
l as r		b.	List the expressions for I _{ds} of an ideal MOS transistor for different regions of oper-	ation. (03 Marks)
eatec		c.	Explain the CMOS inverter DC characteristics highlighting the regions of operation	
jes. be tr		٥.	Explain the Gives in vertex 2 communications and 3	(09 Marks)
k pag will			OR	
blan = 50,	2	a.	With the help of neat diagrams, explain the cutoff, linear and saturation region	on channel
ning :+8=	_		formation in nMOS transistor with different values of V _{gs} and V _{ds} .	(08 Marks)
imaii g, 42		b.	Briefly explain subthreshold condition and geometry dependence with respect to	non-ideal
he re ten e			I-V effects in MOS transistor with relevant expressions.	(08 Marks)
compulsorily draw diagonal cross lines on the remaining blank pages. , appeal to evaluator and /or equations written eg, $42+8=50$, will be			Module-2	
lines tions	3	a.	Draw the stick diagrams for:	
cqua			(i) Simple n-well based BiCMOS inverter	(00) ()
nal ((ii) Logic function $\overline{X} = A + B \cdot C$ in nMOS design style. Draw and explain in brief the design rules for wires in CMOS (λ based).	(08 Marks) (08 Marks)
diago r ano		b.	Draw and explain in oriel the design fules for whes in Cwios (A based).	(00 1111113)
raw (luato			OR	
ily d	4	a.	With the help of relevant figures and expressions, briefly explain the rise time ar	
ulsor eal to		h	estimations with respect to CMOS inverter. With the help of a neat circuit diagram, explain the working of inverting type n	(08 Marks) MOS super
omp		b.	buffer.	(08 Marks)
			CMPIT LIPPARY	
mswe	_	J.	Draw the scaled nMOS transistor highlighting the scaling factors. BANGALORE - 560 037	(06 Marks)
our a	5	a. b.	Derive the scaling factors for the following device parameters:	(00 1/14/185)
ng y		٠.	(i) Gate Capacitance	
pleti			(ii) Maximum Operating Frequency	(05 Marks)
 On completing your answers, c Any revealing of identification 		c.	What are the problems associated with VLSI design? List the ways to reduce then	(05 Marks)
On Any				
e: 1.	96		OR	(06 Mayles)
Not	6	a. b.	Briefly explain the different Bus architectures with necessary figures. Implement the ALU functions line EX-OR, EX-NOR, AND and OR operation	(06 Marks) ons with an
ortant Note: 1. On completing your answers,		υ.	adder. Write the block diagram of 2-bit ALU using adder element.	(10 Marks)

			Module-4	60:
	7	a.	With respect to gate restoration logic, draw the circuit diagram and stick diagram	of 2-input
			NAND gate in nMOS and CMOS logic	(04 Marks)
		b.	Briefly explain Pseudo-nMOS, Dynamic and Clocked CMOS logic.	(06 Marks)
		c.	Design a parity generator and draw its nMOS stick diagram.	(06 Marks)
			OR	
	8	a.	Explain the architecture of FPGA.	(08 Marks)
		Ъ.	With the help of a neat stick diagram, explain the working of 4:1 multiplexer.	(08 Marks)
			Module-5	wassa oot to
	9	a.	Briefly explain the different fault models, observability and controllability with	(10 Marks)
			manufacturing test principles.	(10 Marks)
		b.	List out the System Timing considerations.	(06 Marks)
			On J	
	10		OR	uit diagram
	10	a.		(10 Marks)
		1	and stick diagram.	(06 Marks)
		b.	Briefly explain the Ad-hoc testing.	(00 Marks)

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